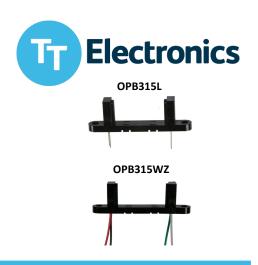
OPB315 Series

Features:

- Lateral package
- Opaque black plastic
- 850 nm wavelength
- Choice of leads or wires



Description:

Each slotted optical switch in this series consists of an infrared emitting diode (LED) and a NPN silicon phototransistor mounted on opposite sides of a 0.90" (22.9 mm) wide slot in an opaque black plastic package.

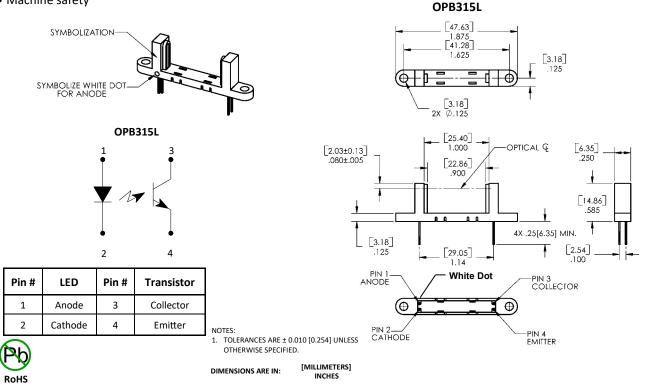
The OPB315L has 0.25" minimum leads, while the OPB315WZ has a minimum of 24" (610 mm) 26 AWG wires.

Phototransistor switching takes place whenever an opaque object passes through the slot.

Applications:

- Non-contact object sensing
- Assembly line automation
- Machine automation
- Equipment security
- Machine safety

Ordering Information							
Part Number	LED Peak Wavelength	Sensor	Slot Width / Depth	Aperture Emitter / Sensor	Wire or Lead Length / Gage		
OPB315L	050	Transistor	0.90"/0.46"	0.03" R / 0.03" R	0.25" / N/A		
OPB315WZ	850 nm				24" min/ 26 AWG wires		



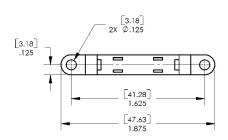
General Note

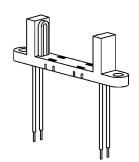
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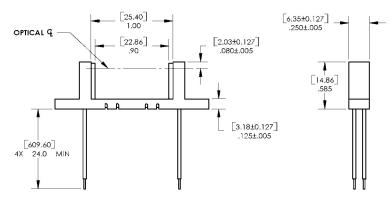
OPB315 Series



OPB315WZ







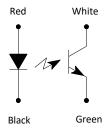
NOTES:

1. TOLERANCES ARE ± 0.010 UNLESS OTHERWISE SPECIFIED.

DIMENSIONS ARE IN:

[MILLIMETERS]
INCHES

OPB315WZ



Pin #/ LED Color		Pin #/ Color	Transistor
Black	Cathode	White	Collector
Red	Anode	Green	Emitter

OPB315 Series



Electrical Specifications

Absolute Maximum Ratings (T_A = 25° C unless otherwise noted)

Storage Temperature Range	-40° C to +80° C
Operating Temperature Range	-40° C to +80° C
Reverse Voltage	2.0 V
Continuous Forward Current	50 mA
Peak Forward Current [measured at 1 μs pulse width and 300 pps]	1.0 A
Lead Soldering Temperature [1/16 inch (1.6 mm) from case for 5 seconds with soldering iron]	260° C ⁽¹⁾⁽²⁾
Power Dissipation (Input Diode)	100 mW
Power Dissipation (Output Phototransistor)	100 mW

Electrical Characteristics (T_A = 25° C unless otherwise noted)

SYMBOL	PARAMETER	MIN	TYP	MAX	UNITS	TEST CONDITIONS	
Input Diode							
V _F	Forward Voltage	-	1.4	1.7	V	I _F = 20 mA	
I _R	Reverse Current	-	-	100	μΑ	V _R = 2 V	
Output Phototransistor (see OP550 for additional information)							
V _{(BR)(CEO)}	Collector-Emitter Breakdown Voltage	30	-	-	٧	I _{CE} = 100 μA, I _F = 0 mA	
V _{(BR)(ECO)}	Emitter-Collector Breakdown Voltage	5.0	-	-	V	$I_{EC} = 100 \mu A$, $I_F = 0 mA$, $E_E = 0$	
I _{CEO}	Collector-Emitter Leakage Current	-	-	100	nA	$V_{CE} = 10.0 \text{ V}, I_F = 0 \text{ mA}, E_E = 0$	
Coupled							
I _{C(ON)}	On-State Collector Current	0.5	1.0	-	mA	V _{CE} = 0.4 V, I _F = 20 mA	
V _{CE(SAT)}	Collector-Emitter	-	-	0.4	V	I _C = 500 μA, I _F = 20 mA	

Notes

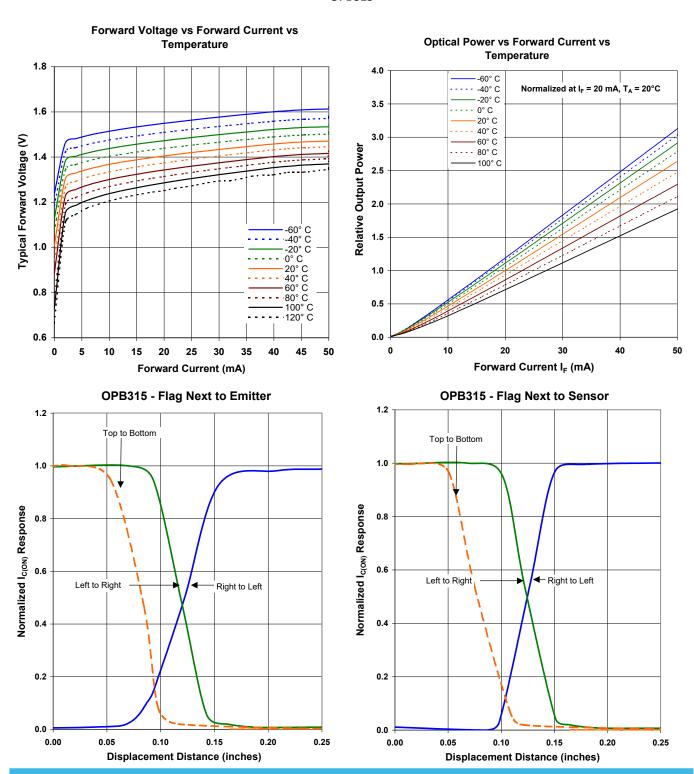
- 1. RMA flux is recommended. Duration can be extended to 10 seconds maximum when flow soldering.
- 2. Derate linearly 1.33 mW/° C above 25° C.

Rev B 10/2016 Page 3

OPB315 Series



OPB315



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